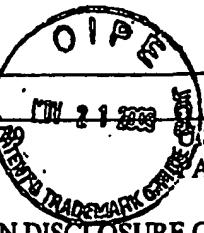


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INFORMATION DISCLOSURE CITATION

Title: MIM Multilayer Capacitor

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APPLICANT - Douglas R. Hackler, Sr. et al.

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
18	03091974 A	17.04.91	Japan				□
19							
20							
21							
22							
23							
24							
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OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication, etc.)

W 26	Kim et al., "Development of CVD-Ru/Ta ₂ O ₅ /CVD-Ru Capacitor with Concave Structure for Multigigabit-scale DRAM Generation," 2001 IEEE, pgs. 12.1.1-12.1.4.
C 27	Aoki et al., "Robust 130nm-Node Cu Dual Damascene Technology with Low-k Barrier SiCN," 2001 IEEE, pgs. 4.2.1-4.2.4.
T 28	Samavati et al., "Fractal Capacitors," IEEE Journal of Solid-State Circuits, Vol. 33, No. 12, December 1998, pgs. 2035-2041.
C 29	Kotecki et al., "(Ba, Sr) TiO dielectrics for future stacked-capacitor DRAM," IBM J. Res. Develop., Vol. 42, No. 3, May 1999, pg. 367-382.
S 30	Media for SolidState Technology, "Interfacial reaction and thermal stability of Ta ₂ O ₅ /TiN for metal electrode capacitors," http://solidstate.articles.printhis.clickability.com/pt/cpt?action=cpt&expire=&urlID=8160 , 11/4/2003, pgs. 1-7.
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